

L Number	Hits	Search Text	DB	Time stamp
1	95	((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:05
2	13	((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicn or si) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:01
3	72	((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicon or si) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:09
4	54	((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicon or si) with substrate)) and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:39
5	0	(substrate near (trench or via)) and ((trench or via) near (trench or via or groove) near (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:40
6	10	(substrate near (trench or via)) and ((trench or via) near (trench or via or groove) with (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:37
7	576	257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 16:39
8	459	(257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:06
9	350	((257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)) and (trench or via or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:03
10	1342	trench adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:04
11	629	(trench adj gate) and (gate near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:04
12	725	(trench adj gate) and (gate near (oxide or sio or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:05
13	260	((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:06
14	206	((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:06

15	117	(((((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and (@ad<20010501)) and ((gate or trench) with (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:12
16	50	(((((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and (@ad<20010501)) and ((gate or trench) with (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:12
-	2	((("5268326") or ("5091330"))).PN.	USPAT; US-PGPUB	2003/01/02 15:55